



# N-CHANNEL ENHANCEMENT MODE MOSFET POWERDI

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
	1.35mΩ @ V <sub>GS</sub> = 10V	150A
30V	$2.4 \text{m}\Omega$ @ $V_{GS} = 4.5 \text{V}$	100A

# Features and Benefits

- Low R<sub>DS(ON)</sub> Minimizes On-State Losses
- Excellent Q<sub>gd</sub> x R<sub>DS(ON)</sub> Product (FOM)
- Advanced Technology for DC-DC Converters
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- 100% Unclamped Inductive Switching Ensures More Reliability
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

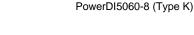
### **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

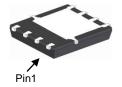
- Backlighting
- Power Management Functions
- DC-DC Converters

#### **Mechanical Data**

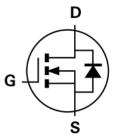
- Case: PowerDI5060-8 (Type K)
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 <a>3</a>
- Weight: 0.097 grams (Approximate)



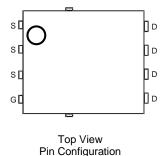




Top View Bottom View



Internal Schematic



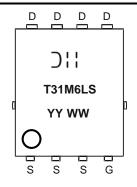
#### Ordering Information (Note 4)

Part Number		Case	Packaging	
	DMT31M6LPS-13	PowerDI5060-8 (Type K)	2,500/Tape & Reel	

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



⊃;; = Manufacturer's Marking
T31M6LS = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 16 = 2016)
WW = Week (01 to 53)



## **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		$V_{DSS}$	30	V
Gate-Source Voltage		$V_{GSS}$	±20	V
Continuous Drain Current, V <sub>GS</sub> = 10V (Note 6)	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	35.8 28.6	А
Continuous Drain Current, $V_{GS} = 10V$ (Note 7) $ T_C = +25^{\circ}C $ $ T_C = +70^{\circ}C $		I <sub>D</sub>	150 128	Α
Maximum Continuous Body Diode Forward Current (Note 7)	I <sub>S</sub>	83	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	160	Α	
Avalanche Current, L=1mH	I <sub>AS</sub>	25.5	А	
Avalanche Energy, L=1mH		E <sub>AS</sub>	325	mJ

## **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	$P_{D}$	1.3	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{ heta JA}$	99	°C/W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	$P_{D}$	2.5	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	50	°C/W	
Total Power Dissipation (Note 7)	T <sub>C</sub> = +25°C	P <sub>D</sub>	100	W
Thermal Resistance, Junction to Case (Note 7)		$R_{ heta JC}$	1.2	°C/W
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

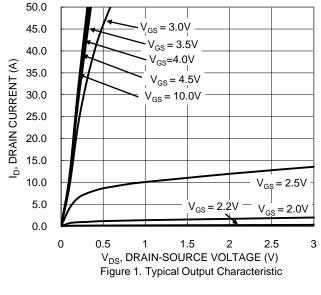
## **Electrical Characteristics** (T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 24V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	-	±100	nA	$V_{GS} = 20V, V_{DS} = 0V$ $V_{GS} = -16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	_	3	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance	Ь		1.1	1.35	mΩ	$V_{GS} = 10V, I_D = 20A$	
Static Dialit-Source Off-Resistance	R <sub>DS(ON)</sub>		1.6	2.4	11122	$V_{GS} = 4.5V, I_D = 20A$	
Diode Forward Voltage	$V_{SD}$	_	_	1.2	V	$V_{GS} = 0V, I_{S} = 2A$	
DYNAMIC CHARACTERISTICS (Note 19)							
Input Capacitance	C <sub>iss</sub>		7019	_			
Output Capacitance	Coss	_	3372	_	pF	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	554	_			
Gate Resistance	$R_{g}$	_	0.94	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V <sub>GS</sub> = 10V)	$Q_g$	_	123	_		V <sub>DD</sub> = 15V, I <sub>D</sub> = 20A	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	$Q_g$	_	59.1	_	nC		
Gate-Source Charge	$Q_{gs}$	_	14.9	_	nc nc		
Gate-Drain Charge	$Q_{gd}$	_	24.5	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	8.6	_			
Turn-On Rise Time	t <sub>R</sub>	_	20.2	_	20	$V_{DD} = 15V, V_{GS} = 10V,$ $R_g = 3\Omega, I_D = 20A$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	71.5	_	ns		
Turn-Off Fall Time	t <sub>F</sub>	_	42.3	_			
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	37.2	_	ns	1 20A dl/dt 500A/us	
Body Diode Reverse Recovery Charge	$Q_{RR}$	_	73.6	_	nC	$I_F = 20A$ , $dI/dt = 500A/\mu s$	

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.





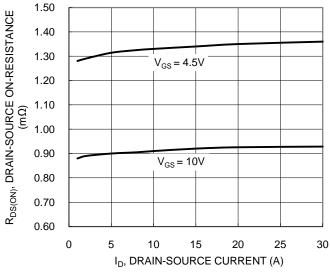


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

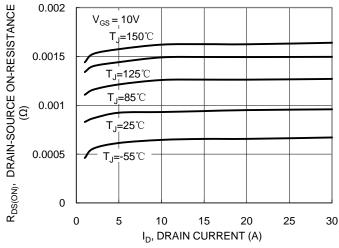
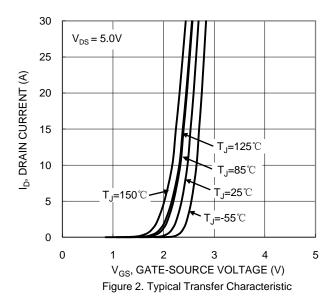


Figure 5. Typical On-Resistance vs. Drain Current and Temperature



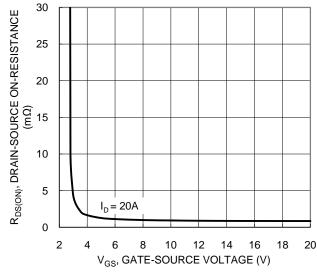


Figure 4. Typical Transfer Characteristic

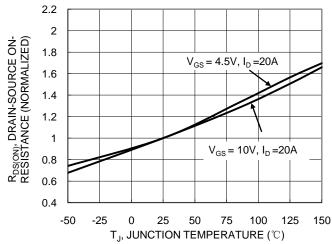


Figure 6. On-Resistance Variation with Temperature





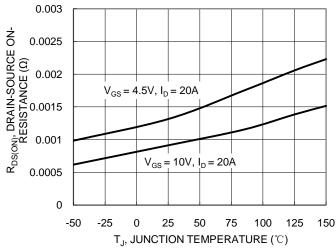
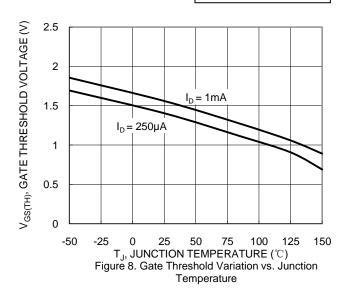
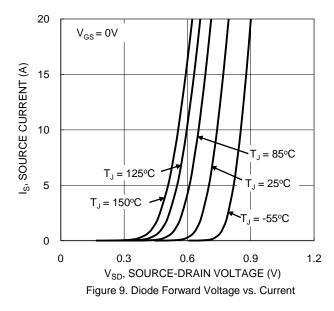
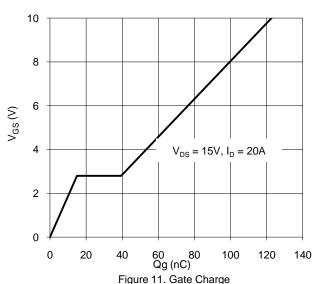


Figure 7. On-Resistance Variation with Temperature







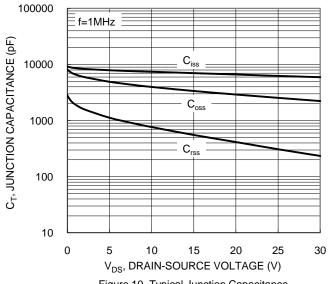


Figure 10. Typical Junction Capacitance

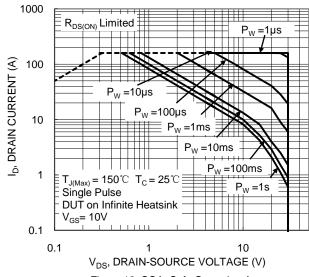


Figure 12. SOA, Safe Operation Area



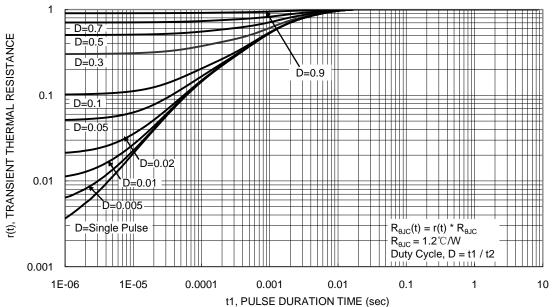


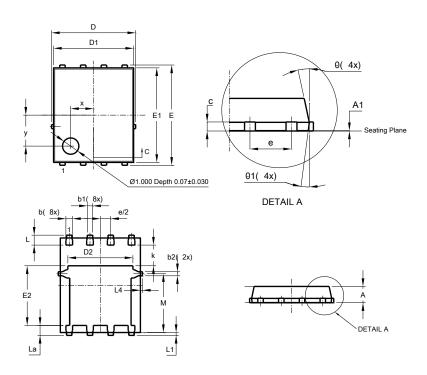
Figure 13. Transient Thermal Resistance



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8 (Type K)

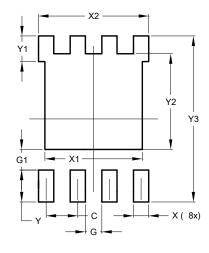


	PowerDI5060-8					
(Type K)						
Dim	Min	Max	Тур			
Α	0.90	1.10	1.00			
A1	0	0.05	0.02			
b	0.33	0.51	0.41			
b1	0.300	0.366	0.333			
b2	0.20	0.35	0.25			
С	0.23	0.33	0.277			
D	5	.15 BS0	)			
D1	4.85	4.95	4.90			
D2	-	-	3.98			
Е	6	.15 BS0	)			
E1	5.75	5.85	5.80			
E2	3.56	3.725	3.66			
Е	1	.27BSC	)			
k	-	-	1.27			
L	0.51	0.71	0.61			
La	0.51	0.675	0.61			
L1	0.05	0.20	0.175			
L4	-	-	0.125			
М	3.50 3.71		3.605			
Х			1.400			
у			1.900			
θ	10°	12°	11°			
θ1	6°	8°	7°			
All Dimensions in mm						

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8 (Type K)



Dimensions	Value (in mm)		
С	1.270		
G	0.660		
G1	0.820		
X	0.610		
X1	3.910		
X2	4.420		
Υ	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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